

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,338,856 B2
APPLICATION NO. : 10/649050
DATED : March 4, 2008
INVENTOR(S) : Chen et al.

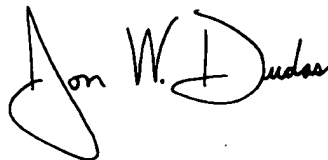
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It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 10, lines 56-58, in Claim 8, delete "introducing dopant atoms of the first type of dopant material into the first polysilicon layer" and insert -- forming the first polysilicon layer --, therefor.

Signed and Sealed this

Sixth Day of January, 2009

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looped initial "J" and a distinct "D" at the end.

JON W. DUDAS
Director of the United States Patent and Trademark Office